

## SMALL SIGNAL SCHOTTKY DIODES


**DESCRIPTION**

General purpose metal to silicon diodes featuring very low turn-on voltage fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

**MINIMELF**  
 (Glass)

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	30	V
$I_F$	Forward Continuous Current	200	mA
$I_{FRM}$	Repetitive Peak Forward Current $t_p \leq 1\text{s}$ $\delta \leq 0.5$	500	mA
$I_{FSM}$	Surge non Repetitive Forward Current	4	A
$P_{tot}$	Power Dissipation	200	mW
$T_{stg}$ $T_j$	Storage and Junction Temperature Range	- 65 to 150 - 65 to 125	°C °C
$T_L$	Maximum Temperature for Soldering during 15s	260	°C

**THERMAL RESISTANCE**

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction-leads	300	°C/W

## ELECTRICAL CHARACTERISTICS

## STATIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
V <sub>(BR)</sub>	T <sub>j</sub> = 25°C	I <sub>R</sub> = 100µA				30	V
V <sub>F</sub> *	T <sub>j</sub> = 25°C	I <sub>F</sub> = 200mA	All Types			1	V
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 10mA	BAT 42			0.4	
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 50mA				0.65	
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 2mA	BAT 43	0.26	0.33		µA
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15mA				0.45	
I <sub>R</sub> *	T <sub>j</sub> = 25°C		V <sub>R</sub> = 25V			0.5	µA
	T <sub>j</sub> = 100°C					100	

## DYNAMIC CHARACTERISTICS

Symbol	Test Conditions				Min.	Typ.	Max.	Unit
C	T <sub>j</sub> = 25°C V <sub>R</sub> = 1V f = 1MHz						7	pF
t <sub>rr</sub>	T <sub>j</sub> = 25°C I <sub>F</sub> = 10mA I <sub>R</sub> = 10mA i <sub>rr</sub> = 1mA R <sub>L</sub> = 100Ω						5	ns
η	T <sub>j</sub> = 25°C R <sub>L</sub> = 15KΩ C <sub>L</sub> = 300pF f = 45MHz V <sub>i</sub> = 2V				80			%

\* Pulse test : t<sub>p</sub> ≤ 300µs δ < 2%.

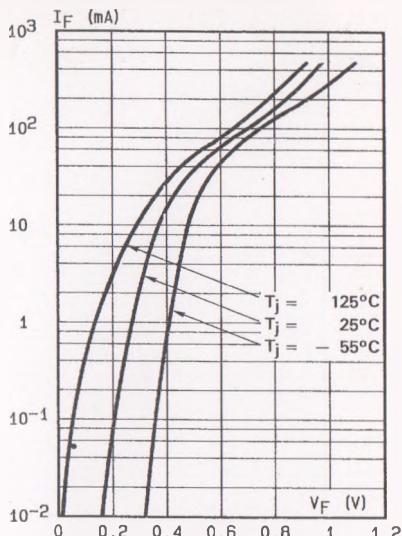


Fig.1 - Forward current versus forward voltage at different temperatures (typical values).

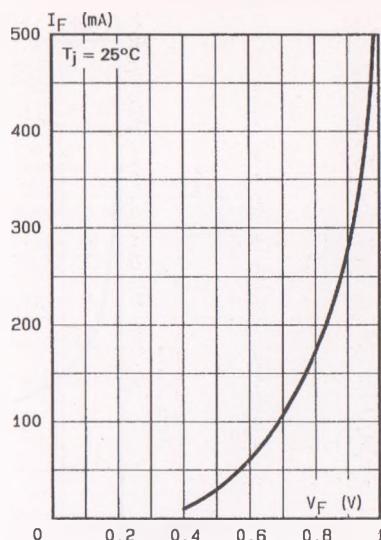


Fig.2 - Forward current versus forward voltage (typical values).

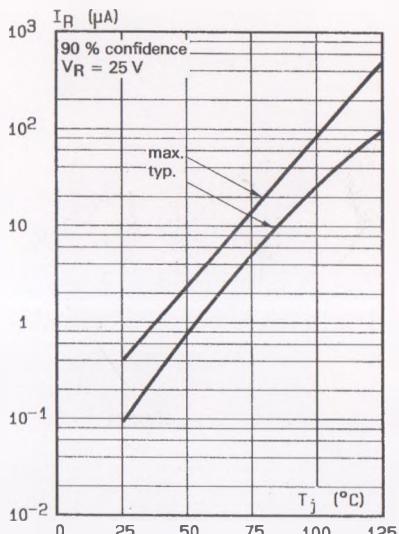


Fig.3 - Reverse current versus junction temperature.

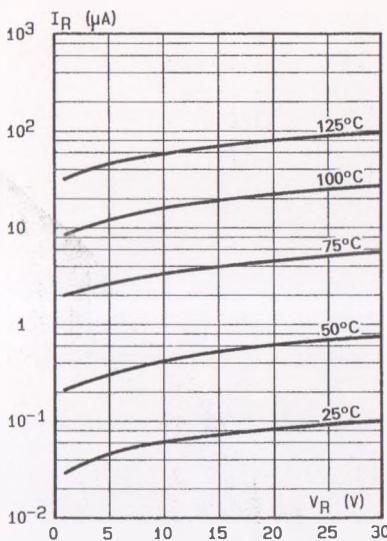


Fig.4 - Reverse current versus continuous reverse voltage (typical values).

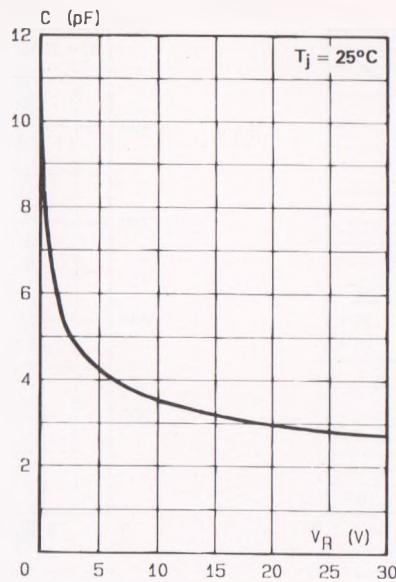


Fig.5 - Capacitance  $C$  versus  
reverse applied voltage  $V_R$   
(typical values).